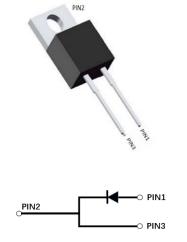


YJD112020PQG3

Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (135°C)}	20A
Q _c	91nC



Features

- Positive temperature coefficient
- Temperature-independent switching
 Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-220AC Molding compound meets UL 94 V-0 flammability
- rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leadsPolarity: As marked

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112020PQG3
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _c =25°C	1	А	44
Continuous forward current @ T _c =135°C	· I _F		20
Non-repetitive peak forward surge current @ T_c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	160
Power Dissipation@ T _c =25°C	P	W	170
Power Dissipation@ T _c =110°C	P _{TOT}	vv	73
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	128
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175



Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drag			I _F =20A, T _j =25°C	1.45	1.55
Forward voltage drop	VF	V _F V	I _F =20A, T _j =175°C	2.1	-
Poverse leakage ourrent			V _R =1200V, T _j =25°C	3	20
Reverse leakage current	I _R	μA	V _R =1200V, T _j =175°C	19	-
Total capacitive charge	Qc	nC	V_R =800V, T _j =25°C , $Q_C = \int_0 {}^{VR} C(V) dV$	91	-
		pF	V _R =0V, f=1MHZ	1280	-
Total capacitance	С		V _R =400V, f=1MHZ	87	-
			V _R =800V, f=1MHZ	64	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	23	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ hetaJ-C}}$	°C W	0.88

■Typical Characteristics

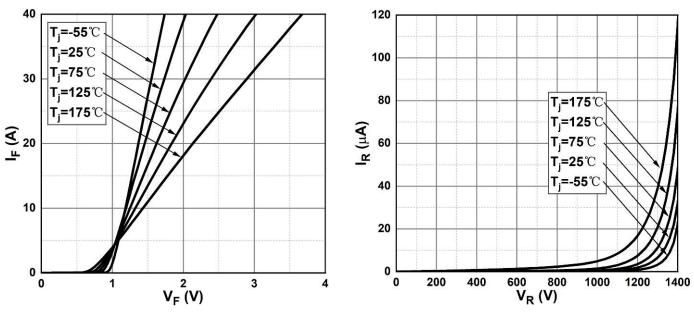
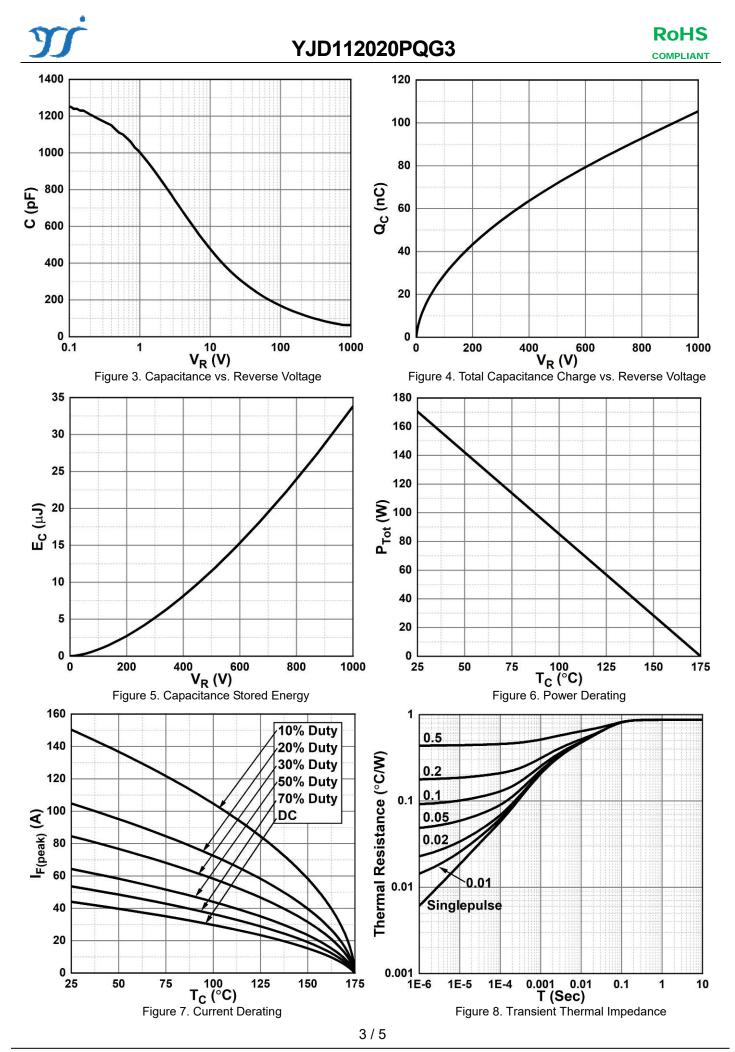


Figure 1. Forward Characteristics

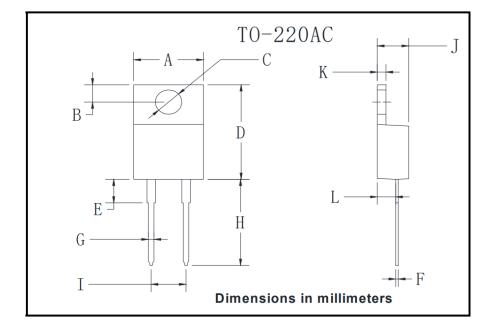
Figure 2. Reverse Characteristics



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Outline Dimensions



TO-220AC				
Dim	Min	Max		
А	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
E	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
н	13.3	13.9		
I	4.86	5.26		
J	4.38	4.78		
К	1.14	1.4		
L	2.37	2.79		



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